

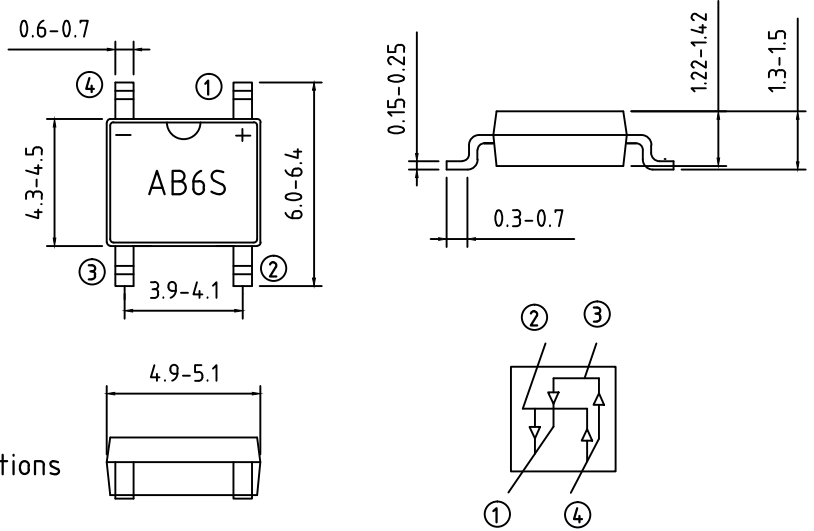
■ 特性 Features

- 玻璃钝化芯片
Glass passivated chip
- 平均整流输出电流为1安培
 $I_o = 1A$
- 反向重复峰值电压为200至1000伏
 $V_{RRM} = 200 \sim 1000V$
- 耐正向浪涌电流能力强
High surge forward current capability

■ 用途 Applications

- 作一般电源单相桥式整流之用
General purpose 1 phase bridge rectifier applications

■ 外型尺寸和标记 Outline Dimensions and Mark



■ 极限值（绝对最大额定值）

Limiting values (Absolute Maximum Rating)

| 参数名称 Item | 符号 Symbol | 单位 Unit | 条件 Conditions | ABS | | | | |
|-----------------------------------------------------|--------------|------------|--------------------------------------------------------------------------------------------------------|-----------------------------------|-----|-----|-----|------|
| | | | | 2 | 4 | 6 | 8 | 10 |
| 反向重复峰值电压 Repetitive Peak Reverse Voltage | V_{RRM} | V | | 200 | 400 | 600 | 800 | 1000 |
| 平均整流输出电流 Average Rectified Output Current | I_o | A | 60Hz正弦波电阻负载, $T_a=25^\circ C$ 60Hz sine wave R-load, $T_a=25^\circ C$ | 安装在氧化铝基板上 On alumina substrate | | 1.0 | | |
| 正向(不重复)浪涌电流 Surge(Non-repetitive)Forward Current | I_{FSM} | A | 60Hz正弦波, 一个周期, $T_j=25^\circ C$ 60Hz sine wave, 1cycle, $T_j=25^\circ C$ | 30 | | | | |
| 正向浪涌电流的平方对电流浪涌的持续时间的积分值 Current Squared Time | I^2t | A^2S | $1ms < t < 8.3ms$, $T_j=25^\circ C$ 单个二极管 $1ms < t < 8.3ms$, $T_j=25^\circ C$ Rating of per diode | 3.7 | | | | |
| 存储温度 Storage Temperature | T_{stg} | $^\circ C$ | | -55~+150 | | | | |
| 结温 Junction Temperature | T_j | $^\circ C$ | | -55~+150 | | | | |

■ 电特性（ $T_a=25$ 除非另有规定）

Limiting values (Absolute Maximum Rating)

| 参数名称 Item | 符号 Symbol | 单位 Unit | 测试条件 Test Condition | 最大值 Max |
|--------------------------------|------------------|--------------|------------------------------------------------------------------------------------------|------------|
| 正向峰值电压 Peak Forward Voltage | V_{FM} | V | $I_{FM}=0.4A$, 脉冲测试, 单个二极管的额定值 $I_{FM}=0.4A$, pulse measurement Rating of per diode | 0.95 |
| 反向峰值电流 Peak Reverse Current | I_{RRM} | μA | $I_{FM}=0.4A$, 脉冲测试, 单个二极管的额定值 $I_{FM}=0.4A$, pulse measurement Rating of per diode | 10 |
| 热阻 Thermal Resistance | $R_{\theta J-A}$ | $^\circ C/W$ | 结和环境之间, 安装在氧化铝基板上 Between junction and ambient, on alumina substrate | 62.5 |
| | $R_{\theta J-L}$ | | 结和引线之间 Between junction and lead | 25 |

Figure 1
Typical Forward Characteristics

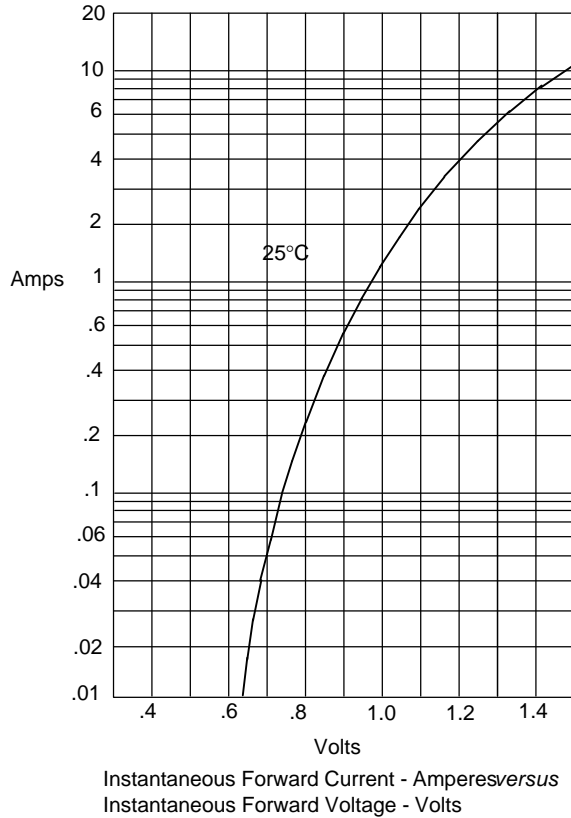


Figure 2
Typical Reverse Characteristics

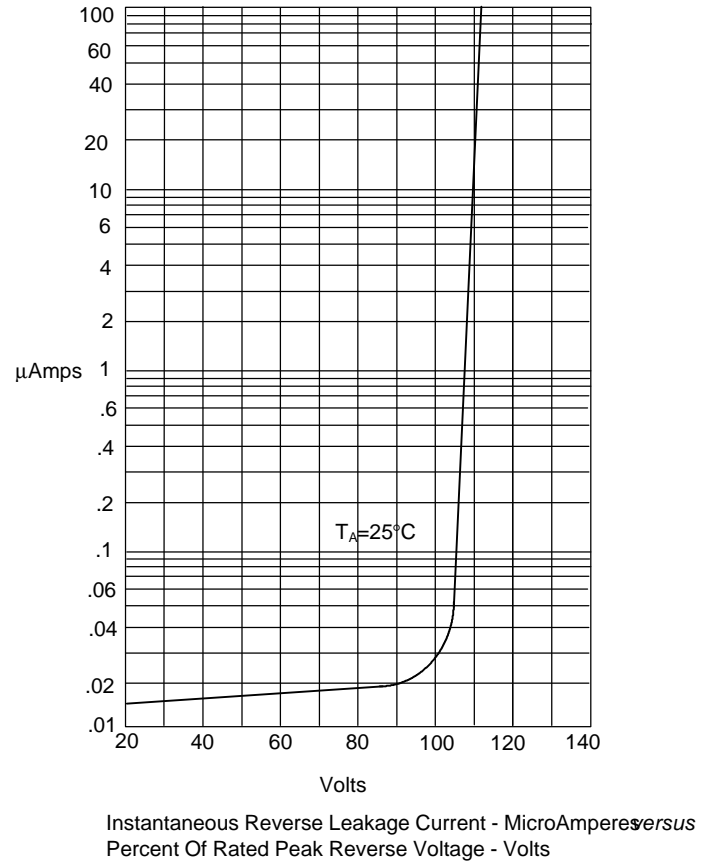


Figure 3
Forward Derating Curve

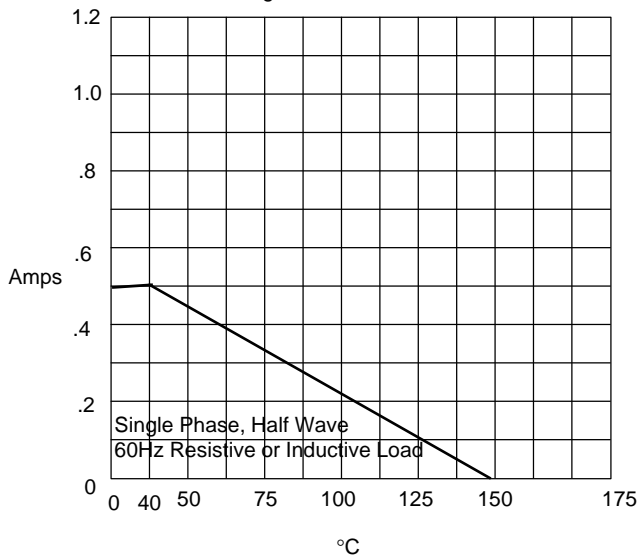


Figure 4
Peak Forward Surge Current

